



MARRI LAXMAN REDDY
INSTITUTE OF TECHNOLOGY AND MANAGEMENT

(AN AUTONOMOUS INSTITUTION)

(Approved by AICTE, New Delhi & Affiliated to JNTUH, Hyderabad)

Accredited by NBA and NAAC with 'A' Grade & Recognized Under Section 2(f) & 12(B) of the UGC act, 1956

III B.Tech II Sem Regular End Examination, June 2022

VLSI Design

(Electronics and Communication Engineering)

Time: 3 Hours.

Max. Marks: 70

Note: 1. Question paper consists: Part-A and Part-B.

2. In Part – A, answer all questions which carries 20 marks.

3. In Part – B, answer any one question from each unit.

Each question carries 10 marks and may have a, b as sub questions.

PART- A

(10*2 Marks = 20 Marks)

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|-------|---------------------------------------------|----|-----|-----|
| 1. a) | Define transconductance and figure of merit | 2M | C01 | BL1 |
| b) | Explain about the CMOS inverter | 2M | C01 | BL4 |
| c) | What are the different MOS layers? | 2M | C02 | BL1 |
| d) | Differentiate two scaling techniques. | 2M | C02 | BL2 |
| e) | Define time delay | 2M | C03 | BL1 |
| f) | Define fan in and fan out | 2M | C03 | BL1 |
| g) | What is pipelining? | 2M | C04 | BL1 |
| h) | Write about the Serial Access Memories | 2M | C04 | BL1 |
| i) | Write any two Test Principles | 2M | C05 | BL1 |
| j) | List the applications of FPGA. | 2M | C05 | BL1 |

PART- B

(10*5 Marks = 50 Marks)

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|------|-------------------------------------------------------|----|-----|-----|
| 2 a) | Explain the nMOS enhancement mode fabrication process | 5M | C01 | BL4 |
| b) | Compare CMOS and Bipolar technologies. | 5M | C01 | BL2 |

OR

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|---|-----------------------------------------------------------------|-----|-----|-----|
| 3 | With neat sketches explain the CMOS n-well fabrication process. | 10M | C01 | BL4 |
|---|-----------------------------------------------------------------|-----|-----|-----|

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|------|-----------------------------------------------|----|-----|-----|
| 4 a) | Explain about CMOS lambda based design rules. | 5M | C02 | BL4 |
| b) | Draw and explain about BICMOS inverter. | 5M | C02 | BL4 |

OR

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|---|---------------------------------------------------------------|-----|-----|-----|
| 5 | Design a stick diagram for two input CMOS NAND and NOR gates? | 10M | C02 | BL6 |
|---|---------------------------------------------------------------|-----|-----|-----|

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|----|-----------------------------------------------------|-----|-----|-----|
| 6 | a) Design XOR gate with CMOS | 5M | C03 | BL6 |
| | b) Explain about the Driving large capacitive loads | 5M | C03 | BL4 |
| | OR | | | |
| 7 | Design NAND and NOR using CMOS | 10M | C03 | BL6 |
| 8 | a) Explain about the ALU | 5M | C04 | BL4 |
| | b) Write in detail about the adders | 5M | C04 | BL1 |
| | OR | | | |
| 9 | Difference between SRAM and DRAM | 10M | C04 | BL2 |
| 10 | a) Draw the typical architecture of PLA and PAL | 5M | C05 | BL1 |
| | b) Difference between PLD and CPLD | 5M | C05 | BL2 |
| | OR | | | |
| 11 | Explain about the Chip level Test Techniques. | 10M | C05 | BL4 |

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